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In collaboration with: Keith Slevin (Osaka University, Japan) Stefan Kettemann (Jacobs University Bremen, Germany)

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- Anderson metal-insulator transitions
- The Anderson-Heisenberg model

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- The kernel polynomial method
- Finite-size scaling of the typical density of states

3 Results for the Anderson-Heisenberg model

4 Conclusions

Effective model for the impurity band electrons in phosphorus-doped silicon

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- Effective model for the impurity band electrons in phosphorus-doped silicon
 - Anderson metal-insulator transitions

Anderson metal-insulator transitions

- Disorder-induced quantum phase transition
- Nonzero disorder: Localized eigenstates appear
- Critical disorder: Phase transition

Density of states (DOS):



 Mobility edges E_M separate band regions of localized and extended states

Anderson (1958)





Anderson model: Constant NN hopping, random site-potentials

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Anderson (1958)



Anderson model: Constant NN hopping, random site-potentials Rodriguez et al. (2011)



Critical eigenstate $\left|\psi^{2}\right| \sim L^{-lpha}$

(broad distribution of α , maximum at α_0)

 \rightarrow Multifractality

- Effective model for the impurity band electrons in phosphorus-doped silicon
 - The Anderson-Heisenberg model

The Anderson-Heisenberg model

- Si:P exhibits a metal-insulator transition, driven by both interaction and disorder
- Further, local magnetic moments have been found

How do the local magnetic moments influence the transition?

Start from Anderson model:

$$extsf{H}_{0} = t \sum_{\langle i,j
angle,\sigma} \ket{j,\sigma} ra{i,\sigma} + \sum_{i,\sigma} arepsilon_{i} \ket{i,\sigma} ra{i,\sigma}$$

 Add local exchange coupling to classical magnetic impurities:

$$\label{eq:H_s_s_s} \mathtt{H} = \mathtt{H}_0 + \mathtt{H}_{\mathrm{s}} \quad, \quad \mathtt{H}_{\mathrm{s}} = \sum_i J_i \, \textbf{s}_i \cdot \textbf{S}_i$$





- Has been introduced as an effective model for the impurity band electrons in Si:P
- Fix concentration of sites carrying a magnetic moment to $n_{\rm M}=5\,\%$
- Compare Heisenberg impurities (random orientation, unitary symmetry) to Ising impurities (only ↑↓, orthogonal symmetry)

Anderson (1958); Bhatt and Rice (1981); Sachdev (1989); von Löhneysen (2000)

- Numerical methods

L The kernel polynomial method

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L The kernel polynomial method

The kernel polynomial method

Use Chebychev expansion to approximate the local density of states:

$$ilde{
ho}_i(ilde{E}) = rac{1}{\pi\sqrt{1- ilde{E}^2}} \left(\mu_0^{(i)} + 2\sum_{m=1}^M \mu_m^{(i)} \; \mathcal{T}_m(ilde{E})
ight)$$

Truncation limit: Finite number M of coefficients $\mu_m^{(i)}$

Chebychev polynomials of first kind:

$$T_m(x) = \cos(m \arccos x)$$

Recursive relations (CP of first kind):

$$T_0(x) = 1$$
 , $T_1(x) = x$
 $T_{m+1}(x) = 2x T_m(x) - T_{m-1}(x)$

Chebychev moments $\mu_m^{(i)}$ for the LDOS:

$$\mu_m^{(i)} = \frac{1}{N} \langle i | T_m(\tilde{H}) | i \rangle$$



KPM approximation causes an energy broadening η . At $\tilde{E} = 0$:

$$\tilde{\eta} \approx \frac{\pi}{M}$$

Weiße et al. (2006)

-Numerical methods

Finite-size scaling of the typical density of states

The typical density of states

Typical density of states

 Geometric average over the local density of states

 $ho_{\mathrm{typ}}(E) = \exp \langle \log \rho_i(E) \rangle_{\mathrm{dis}}$

- Scales with W, L, M
- Thermodynamic limit:

$$\lim_{L \to \infty} \rho_{\rm typ} = \begin{cases} 0 & \quad \text{localized} \\ \text{const} & \quad \text{extended} \end{cases}$$

 \rightarrow Critical at the MIT

Can the typical density of states be used to determine the MIT?

- Numerical methods

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Yes, but: For finite system size, no clear distinction possible.

One would need a cutoff...



How to choose a suitable cutoff? Adjustment to external calibration parameter necessary...

Schubert and Fehske (2009)

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Finite-size scaling of the typical density of states

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Local density of states (with finite broadening η):

$$\rho(\boldsymbol{E}, \mathbf{r}, \eta) = \sum_{k} |\psi_{k}(\mathbf{r})|^{2} \,\delta(\boldsymbol{E} - \boldsymbol{E}_{k}, \eta)$$

Geometric average of local density of states:

$$\rho_{\rm typ}(E) = \exp \langle \log \rho_i(E) \rangle$$

At criticality:

$$ho_{\mathrm{typ}} \sim L^{d-\alpha_0}$$

Janssen (1998)

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Two scales:

- Length scale: L/ξ L/ξ < 1: State critical</p>
 - $L/\xi > 1$: State localized or extended
- Energy scale: η/Δ $\eta/\Delta \rightarrow 0$: High resolution limit $\eta/\Delta \rightarrow \infty$: Low resolution limit

-Numerical methods

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Scaling ansatz:

$$\Gamma = L^{d-\alpha_0} F(L/\xi, \eta/\Delta)$$

Alternative form:

$$\Gamma = L^{d-\alpha_0} F(\varepsilon L^{\frac{1}{\nu}}, \rho_{\rm av} \eta L^d)$$

$$\Gamma(E) = rac{
ho_{
m typ}(E)}{
ho_{
m av}(E)} ~,~~ arepsilon = rac{{
m W_c}-{
m W}}{{
m W_c}}$$

- Numerical methods

Finite-size scaling of the typical density of states

Validity of the scaling ansatz – First argument

 \rightarrow Keep second argument $\rho_{\rm av} \eta L^d$ fixed.

Approximation: We fix ηL^d and neglect the disorder dependence of $\rho_{av}(E)$.

$$\Gamma(W,L) = L^{\alpha_0 - d} \tilde{F}(\varepsilon L^{rac{1}{
u}}) \quad , \quad \varepsilon = rac{\mathrm{W_c} - \mathrm{W}}{\mathrm{W_c}}$$

 \rightarrow Consider a power law for $\tilde{F}(x)$ (second order)



 \rightarrow General validity proven for the 3D Anderson model

ightarrow Obtain $W_{
m c}$, $lpha_0$ and u as fit parameters

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Impact of Local Magnetic Moments on the Anderson Metal-Insulator Transition Results for the Anderson-Heisenberg model

The Anderson-Heisenberg model: Fitting results

Apply scaling ansatz to the Anderson-Heisenberg model, vary exchange coupling JFit results:



 \rightarrow Expectations qualitatively met Exception: Loc. length exp. ν

Jung, Slevin, and Kettemann (2014), unpublished

Results for the Anderson-Heisenberg model

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Effective model for the impurity band electrons in materials like Si:P



- Use kernel polynomial method to efficiently calculate the local density of states
- Finite-size scaling of the typical density of states to estimate critical parameters
- Compare influence of Heisenberg and lsing impurities on the Anderson metal-insulator transition

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Outlook:

- Improve finite-size scaling analysis for quantitative estimation of critical parameters
- Quantitative analysis of the shift of the critical disorder W_c with increasing exchange coupling J
- Obtain full phase diagrams
 First attempt:



- Conclusions

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Thank you for your attention!

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The Anderson-Heisenberg model

Full Hamiltonian:

 $\mathtt{H}=\mathtt{H}_0+\mathtt{H}_{\mathrm{s}}$

Anderson model (with spin):

$$\mathtt{H}_{0} = t \sum_{\langle i,j \rangle, \sigma} \left| j, \sigma \right\rangle \left\langle i, \sigma \right| + \sum_{i,\sigma} \left. \varepsilon_{i} \right. \left| i, \sigma \right\rangle \left\langle i, \sigma \right|$$

Exchange coupling to classical magnetic impurities:

$$\mathbf{H}_{\mathrm{s}} = \sum_{i} J_{i} \, \mathbf{s}_{i} \cdot \mathbf{S}_{i}$$

Pauli matrices:

$$\sigma_1 = \begin{pmatrix} 0 & 1 \\ 1 & 0 \end{pmatrix} \quad , \quad \sigma_2 = \begin{pmatrix} 0 & -i \\ i & 0 \end{pmatrix} \quad , \quad \sigma_3 = \begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$$

Alternative formulation:

$$\mathtt{H}_{\mathrm{s}} = S \sum_{i=1}^{N} J_{i} \left(\cos \theta_{i} \sum_{\sigma = \pm 1} \sigma \left| i, \sigma \right\rangle \left\langle i, \sigma \right| + \sin \theta_{i} \sum_{\sigma = \pm 1} \exp(i \sigma \varphi_{i}) \left| i, \sigma \right\rangle \left\langle i, -\sigma \right| \right)$$



 $\mathbf{s}_i = \frac{\hbar}{2}\sigma_i$

Detailed calculation of Chebychev moments

Chebychev moments for the LDOS:

$$\begin{split} \mu_m^{(i)} &= \int_{-1}^1 \tilde{\rho}_i(\tilde{E}) \ T_m(\tilde{E}) \ \mathsf{d}\tilde{E} \\ &= \frac{1}{N} \sum_{k=0}^{N-1} |\langle i|k \rangle|^2 \int_{-1}^1 T_m(\tilde{E}) \ \delta(\tilde{E} - \tilde{E}_k) \ \mathsf{d}\tilde{E} \\ &= \frac{1}{N} \sum_{k=0}^{N-1} |\langle i|k \rangle|^2 \ T_m(\tilde{E}_k) \\ &= \frac{1}{N} \sum_{k,k'=0}^{N-1} \langle i|k \rangle \ \langle k|T_m(\tilde{H})|k' \rangle \ \langle k'|i \rangle \\ &= \frac{1}{N} \ \langle i|T_m(\tilde{H})|i \rangle \end{split}$$

Chebychev moments for the DOS:

$$\mu_{m} = \int_{-1}^{1} \tilde{\rho}(\tilde{E}) T_{m}(\tilde{E}) d\tilde{E}$$
$$= \frac{1}{N} \sum_{k=0}^{N-1} \int_{-1}^{1} T_{m}(\tilde{E}) \delta(\tilde{E} - \tilde{E}_{k}) d\tilde{E}$$
$$= \frac{1}{N} \sum_{k=0}^{N-1} T_{m}(\tilde{E}_{k})$$
$$= \frac{1}{N} \sum_{k=0}^{N-1} \langle k | T_{m}(\tilde{H}) | k \rangle$$
$$= \frac{1}{N} \operatorname{Tr} T_{m}(\tilde{H})$$

Weiße et al. (2006)

Sample variance of the geometric mean I

The arithmetic mean \bar{x} of a discrete random variable x is defined as

$$\bar{x} = \frac{1}{N} \sum_{i=1}^{N} x_i \quad , \tag{1}$$

where N is the sample size. It is a good estimator for the population mean. Its (unbiased) sample variance is well known,

$$\sigma_x^2 = \frac{1}{N-1} \sum_{i=1}^N (x_i - \bar{x})^2 = \frac{\overline{x^2}}{N-1} - \frac{\bar{x}^2}{N(N-1)} \quad . \tag{2}$$

We introduce the quantity y, which is defined as the logarithm of the random variable x, $y = \log x$. Its arithmetic mean and variance is calculated according to (1) and (2),

$$\bar{y} = \overline{\log x} = \frac{1}{N} \sum_{i=1}^{N} \log x_i \quad ,$$

$$\sigma_y^2 = \sigma_{\log x}^2 = \frac{1}{N-1} \sum_{i=1}^{N} (\log x_i - \overline{\log x})^2 = \frac{\overline{(\log x)^2}}{N-1} - \frac{\overline{\log x}^2}{N(N-1)}$$

Sample variance of the geometric mean II

Now, the geometric mean of x is

$$z = e^{\overline{\log x}} = e^{y}$$

We estimate the statistical error of z, given by its standard deviation σ_z , by

$$\sigma_z = z_1 - z_2 = \mathrm{e}^{\bar{y}} (\mathrm{e}^{\sigma_y} - 1)$$

 $egin{aligned} z_1 &= \mathrm{e}^{ar{y} + \sigma_y} \ z_2 &= \mathrm{e}^{ar{y}} \end{aligned}$

with

Assuming σ_{v} to be small, we approximate

$$\sigma_z = \mathrm{e}^{\bar{y}}(\mathrm{e}^{\sigma_y} - 1) pprox \mathrm{e}^{\bar{y}}\sigma_y$$

and hence the estimate of the sample variance of the geometric mean is given by

$$\sigma_z^2 \approx \mathrm{e}^{2\bar{y}} \sigma_y^2$$

The same result has been obtained by Norris $\,$ Norris (1940) using more profound mathematical arguments.

The Anderson model I

Anderson model:

$$\mathtt{H} = t \sum_{\langle ij
angle} (c_i^\dagger c_j + c_j^\dagger c_i) + \sum_i arepsilon_i c_i^\dagger c_i$$

Random potentials ε_i :



W: Measure for disorder

The Anderson model I

Anderson model:

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angle} (c_i^{\dagger} c_j + c_j^{\dagger} c_i) + \sum_i \varepsilon_i c_i^{\dagger} c_i$$

Random potentials ε_i :



W: Measure for disorder

What happens if translational symmetry gets lost?

 \rightarrow Bloch theory not applicable anymore

Density of states:



 \rightarrow Bandwidth increases with W \rightarrow Van-Hove singularities disappear

The Anderson model II

Emergence of localized states in the band tails.

W > 0: Localized states emerge



Mobility edges $E_{\rm M}$: Separating energies of localized and extended states

Critical disorder $W_{\rm c}$: Mobility edges collapse in the band center

 \rightarrow Metal-insulator transition

The Anderson model II

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Phase diagram:



 \rightarrow Mobility edge as function of disorder Bulka et al. (1987)

3D Anderson model: Visualizing eigenstates

Wave function intensity, $N = 120^3$, E = 0



Rodriguez et al. (2011)

3D Anderson model: Visualizing eigenstates

Wave function intensity, $N = 120^3$, E = 0



Multifractality

Electronic wave functions at the MIT are multifractal.

Fractals:

- Self-similarity on all scales
- Fractal dimension D, not necessarily integer

Multifractal objects:

More than one fractal dimension D

Wave function intensity:

$$\left|\psi(\mathbf{r})\right|^2 \sim L^{-\alpha}$$

Broad distribution of exponents α :

$$P(\alpha) = L^{-\frac{(\alpha - \alpha_0)^2}{4(\alpha_0 - d)}}$$

Evers and Mirlin (2008); Kettemann et al. (2009)

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Evers and Mirlin (2008); Kettemann et al. (2009)

Singularity spectrum $f(\alpha)$:



 \rightarrow Approximately parabolic, with maximum at α_0

Interpretation of $f(\alpha)$: Fractal dimension of those points in space where the WFI scales like $L^{-\alpha}$.

Multifractal analysis: Obtain critical parameters of the MIT with high precision

Kernel damping

The Gibbs phenomenon

- Strong oscillations near sharp features (sharp peaks, discontinuities)
- Solution: Multiply Chebychev moments by kernel factors

Dirichlet kernel (trivial case):

$$g_m^{\rm D} = 1$$

Jackson kernel (best for DOS and LDOS):

$$g_m^{
m J} = rac{(M-m+1)\cosrac{\pi m}{M+1} + \sinrac{\pi m}{M+1}\cotrac{\pi}{M+1}}{M+1}$$





Apply kernel:

 $\mu_m \rightarrow g_m \mu_m$

Weiße et al. (2006)

Spectral dependence of the energy resolution

KPM + Jackson kernel

$$ilde{\eta}(ilde{E}) = \sqrt{rac{M - ilde{x}^2(M-1)}{2(M+1)}(1 - \cos(2\phi))} pprox rac{\pi}{M} \sqrt{1 - ilde{x}^2 + rac{4 ilde{x}^2 - 3}{M}} \quad , \quad \phi = \pi/(\mathrm{M}+1)$$

Simple form at $\tilde{x} = 0$: $\tilde{\eta} \approx \frac{\pi}{M}$ $\eta \approx \frac{\pi}{M}$ $\eta \approx \frac{\pi}{M}$

Possibility to adjust the truncation limit *M* to keep η constant \rightarrow Variable-moment KPM (VMKPM)

Schubert and Fehske (2009)